

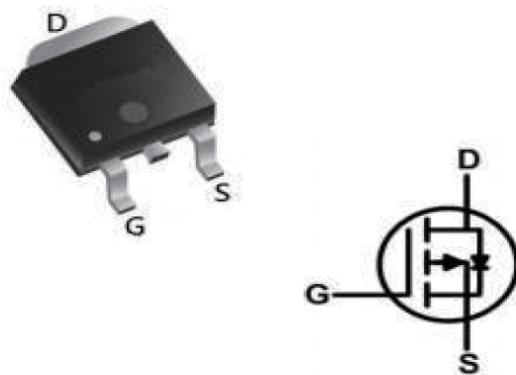
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed

**Product Summary**
**RoHS**

BVDSS	RDSON	ID
-40V	31mΩ	-23A

**Description**

The 25P04 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and gate charge for most of the synchronous buck converter applications. The 25P04 meets the RoHS and Green Product requirement 100% EAS Guaranteed with full function reliability approved.

**TO252 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit	
V <sub>DSS</sub>	Drain-Source Voltage	-40	V	
V <sub>GSS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Continuous Drain Current	T <sub>c</sub> = 25°C T <sub>c</sub> = 100°C	-23 -12	A A
I <sub>DM</sub>	Pulsed Drain Current <small>note1</small>	-40	A	
E <sub>AS</sub>	Single Pulsed Avalanche Energy <small>note2</small>	27.6	mJ	
P <sub>D</sub>	Power Dissipation	T <sub>c</sub> = 25°C	8	W
R <sub>θJC</sub>	Thermal Resistance, Junction to Case		18.8	°C/W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

Electrical Characteristics ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

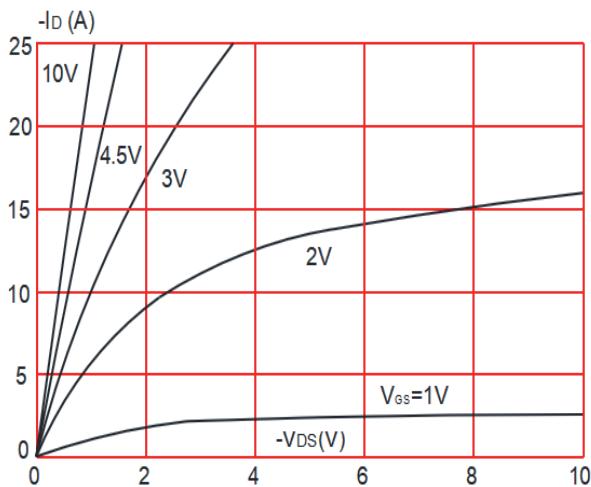
Symbol	Parameter	Test condition	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D = -250\mu\text{A}$	-40	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -40\text{V}$ , $V_{GS}=0\text{V}$	-	-	-1	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0\text{V}$ , $V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D = -250\mu\text{A}$	-1	-1.6	-2.5	V
$R_{DS(\text{on})}$ <small>note3</small>	Static Drain-Source on-Resistance	$V_{GS} = -10\text{V}$ , $I_D = -8\text{A}$	-	31	44	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}$ , $I_D = -5\text{A}$	-	44	60	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -20\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	1034	-	pF
$C_{oss}$	Output Capacitance		-	107	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	79.5	-	pF
$Q_g$	Total Gate Charge	$V_{DS} = -20\text{V}$ , $I_D = -5\text{A}$ , $V_{GS} = -10\text{V}$	-	20	-	nC
$Q_{gs}$	Gate-Source Charge		-	3.5	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	4.2	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -20\text{V}$ , $I_D = -5\text{A}$ , $V_{GS} = -10\text{V}$ , $R_{GEN} = 2.5\Omega$	-	8	-	ns
$t_r$	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	23	-	ns
$t_f$	Turn-off Fall Time		-	9	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_s$	Maximum Continuous Drain to Source Diode Forward Current	-	-	-23	-	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	-40	-	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$ , $I_s = -10\text{A}$	-	-0.8	-1.2	V
$trr$	Reverse Recovery Time	$V_{GS} = 0\text{V}$ , $I_S = -5\text{A}$ , $dI/dt = 100\text{A}/\mu\text{s}$	-	29	-	ns
$Qrr$	Reverse Recovery Charge		-	20	-	nC

## Notes:

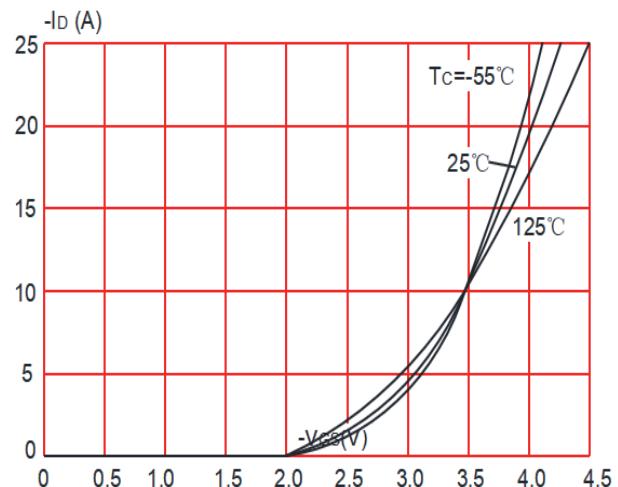
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- 2.EAS condition:  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = -20\text{V}$ ,  $V_G = -10\text{V}$ ,  $L = 0.5\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = -10.5\text{A}$
- 3.Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

### Typical Electrical and Thermal Characteristics (Curves)

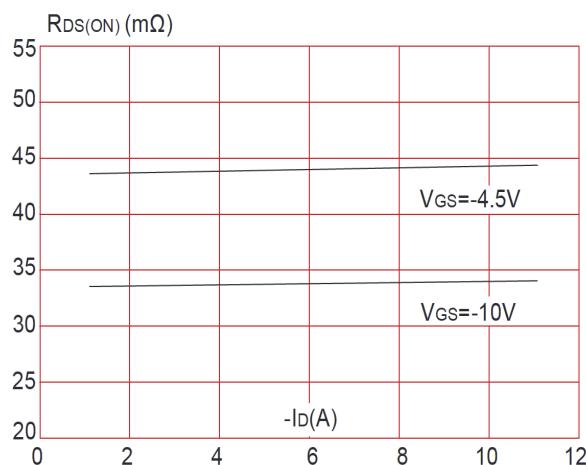
**Figure1: Output Characteristics**



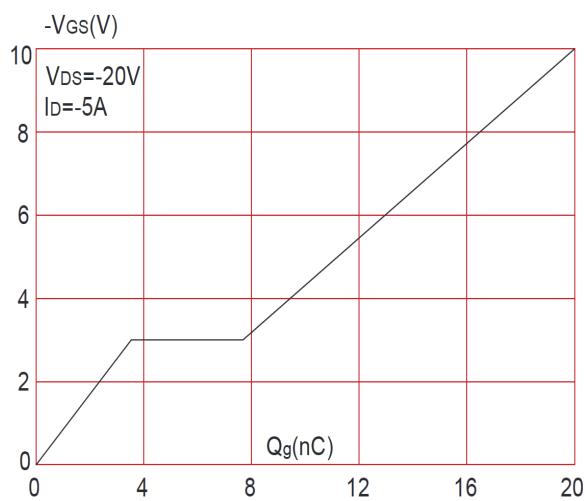
**Figure 2: Transfer Characteristics**



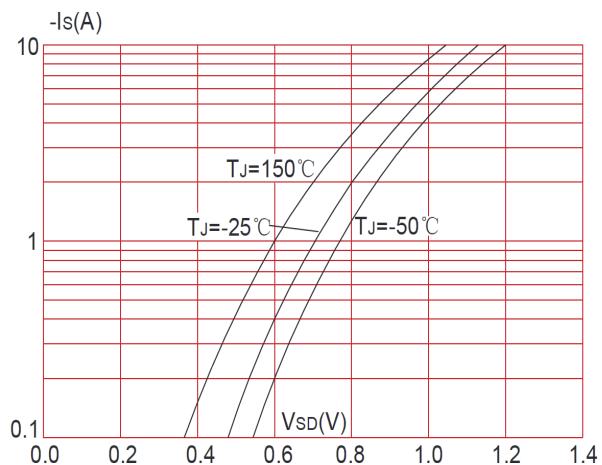
**Figure 3:On-resistance vs. Drain Current**



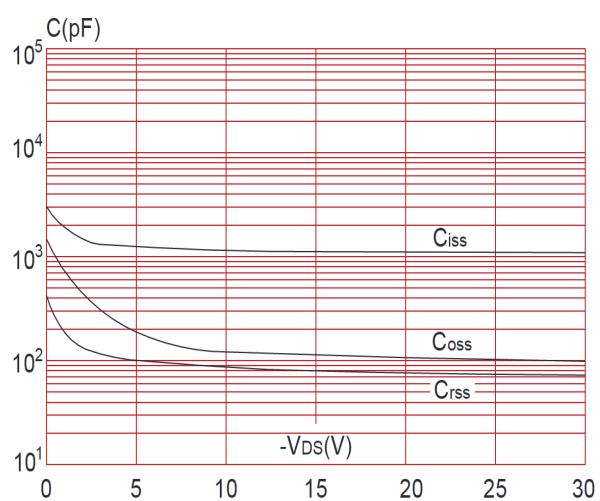
**Figure 5: Gate Charge Characteristics**



**Figure 4:Body Diode Characteristics**

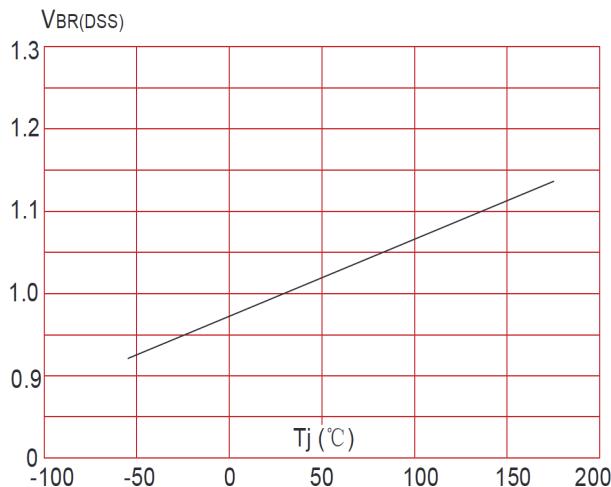


**Figure 6:Capacitance Characteristics**

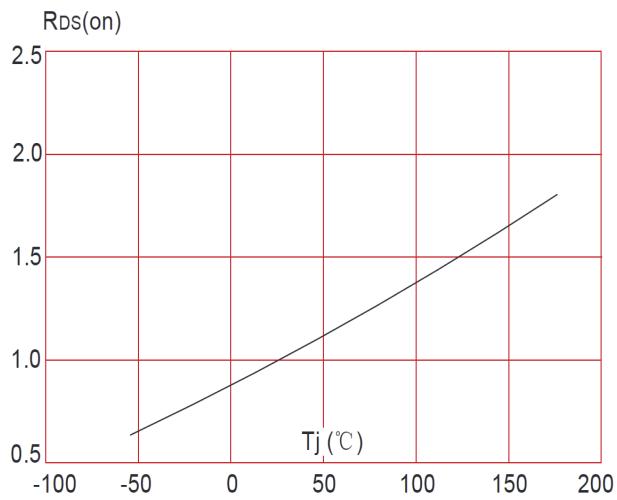


### Typical Performance Characteristics

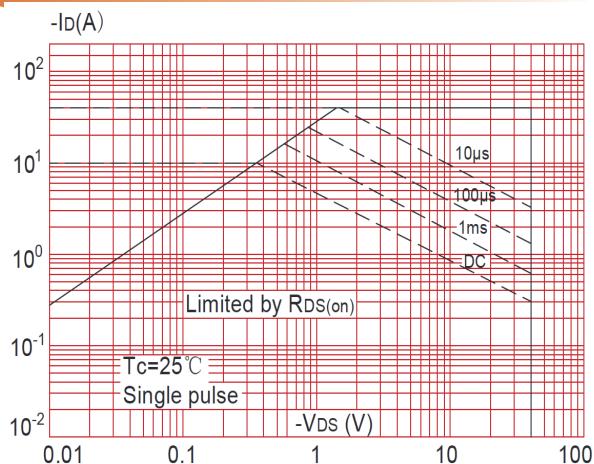
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



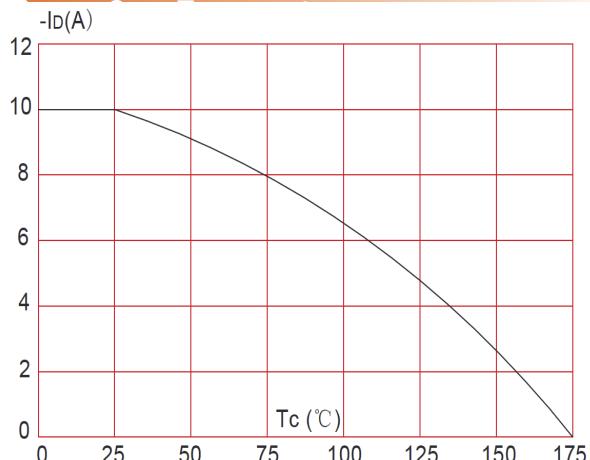
**Figure 8: Normalized on Resistance vs. Junction Temperature**



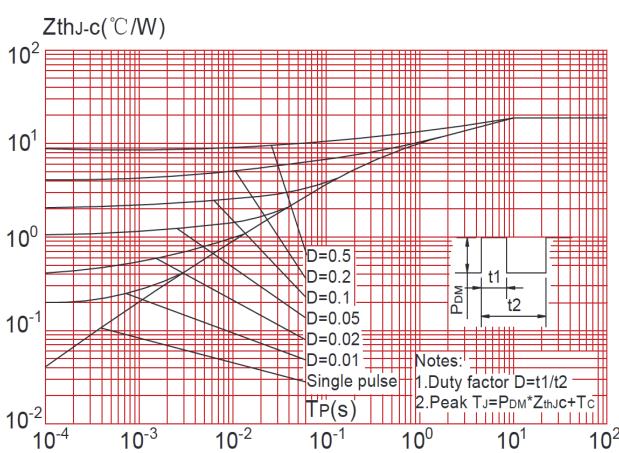
**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**



**Figure 11: Maximum Effective Transient Thermal Impedance Junction to Case**



## Test Circuit

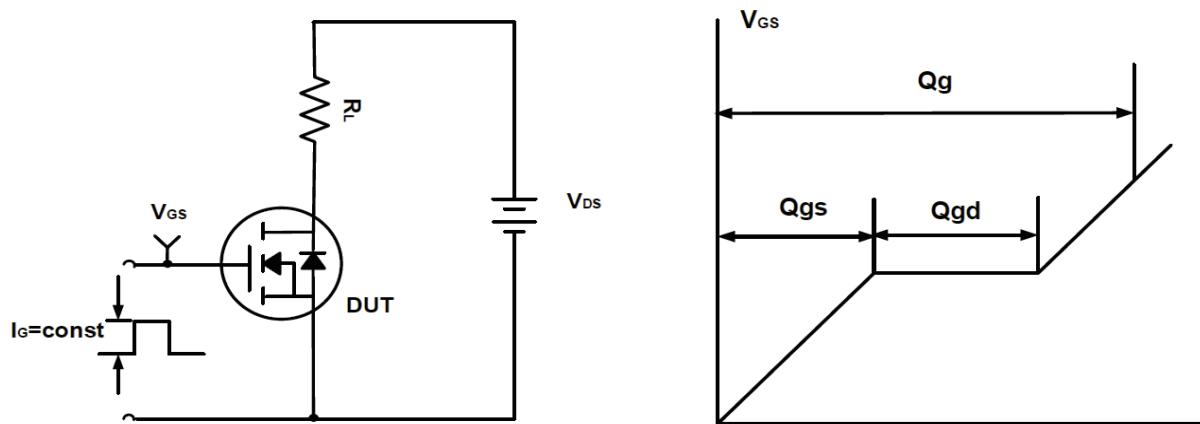


Figure A. Gate Charge Test Circuit & Waveforms

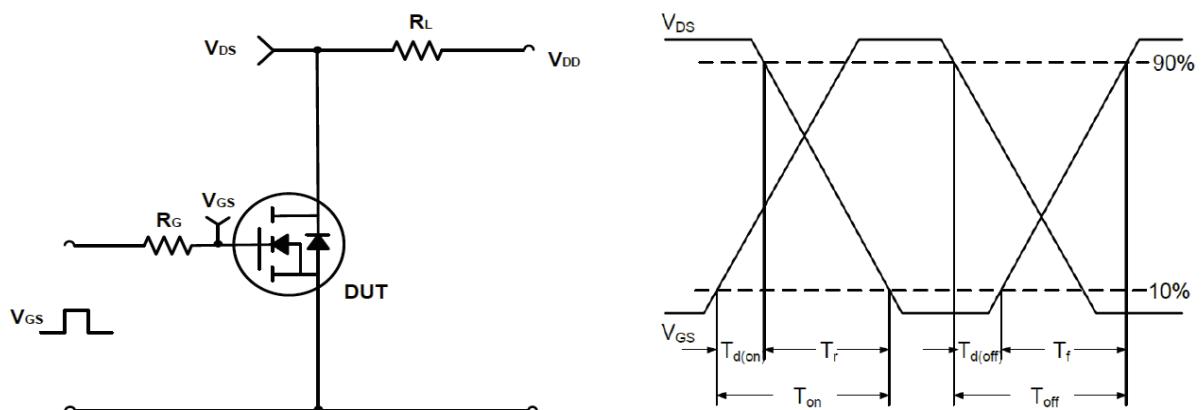


Figure B. Switching Test Circuit & Waveforms

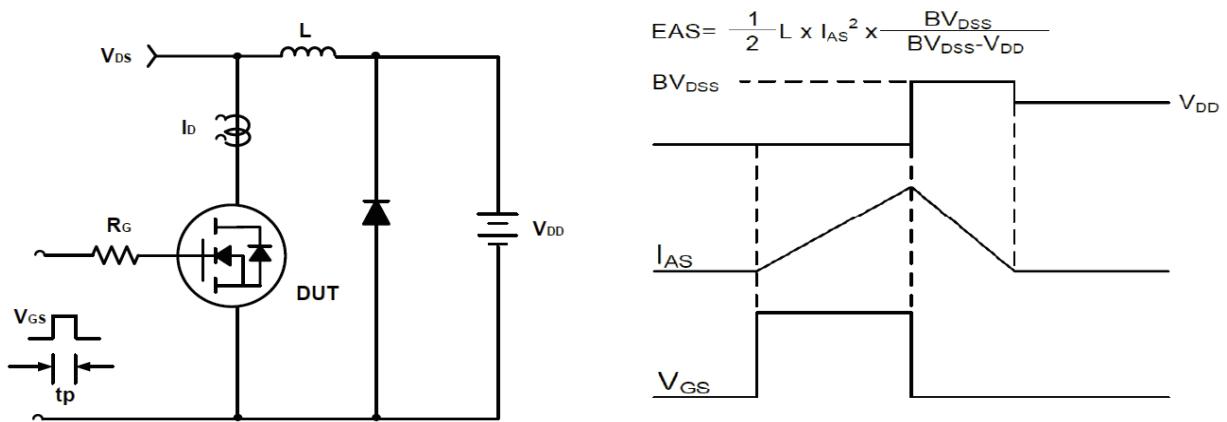
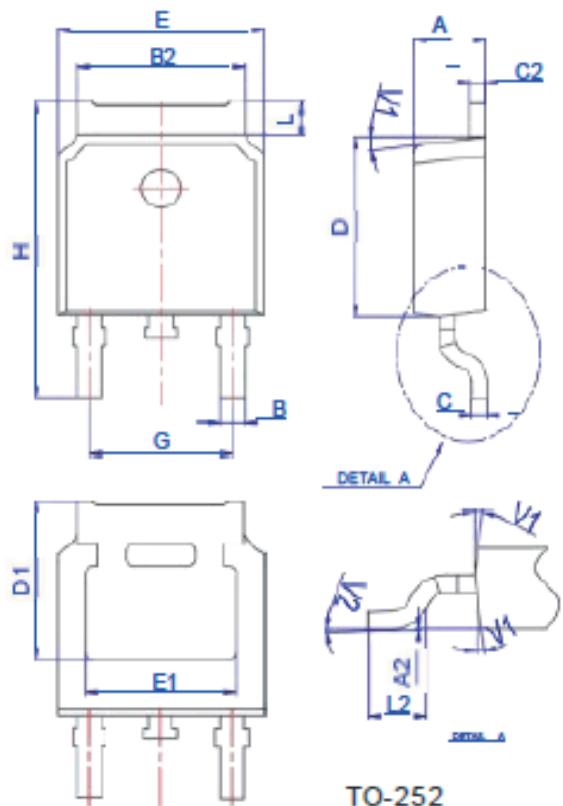


Figure C. Unclamped Inductive Switching Circuit & Waveforms

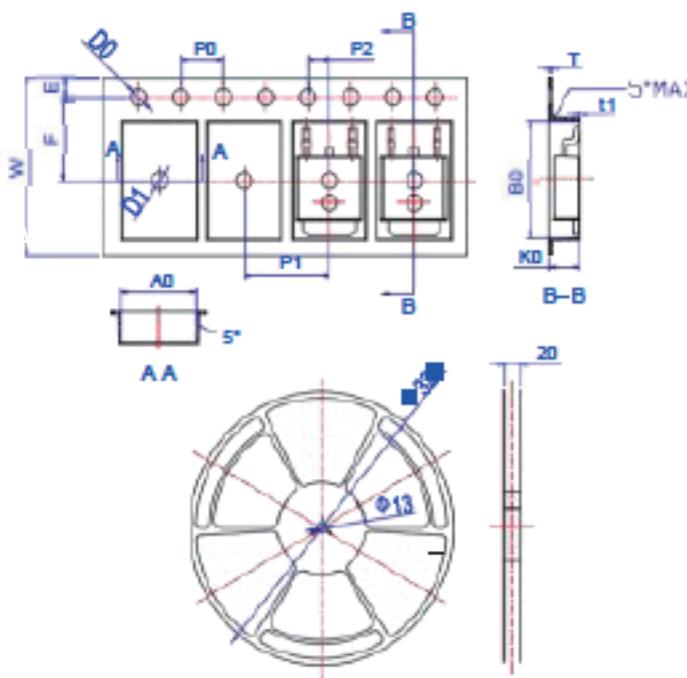
## Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

TO-252

## Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
KD	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583